HTIRC-03-005

JAN 2 9 2004 8

January 22, 2004

To: Commissioner for Patents

P.O.Box 1450

Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572

28 Davis Avenue

Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/714,305 11/14/03

Jei-Wei Chang et al.

SINGLE LAYER RESIST LIFTOFF PROCESS

FOR NANO TRACK WIDTH

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on January >7, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

HTIRC-03-005

- U.S. Patent 6,519,124 to Redon et al., "Magnetic Tunnel Junction Read Head Using a Hybrid, Low-Magnetization Flux Guide," discloses a conventional lift-off resist process.
- U.S. Patent 5,212,044 to Liang et al., "Photoresist Composition Including Polyphenol and Sensitizer," describes a method of hardening a resist using an ion beam.

Sincerely,

Stephen B. Ackerman,

Reg. No. 37761